

SemiNex delivers the highest available power at infrared wavelengths between 13xx and 17xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements

## Laser Bars

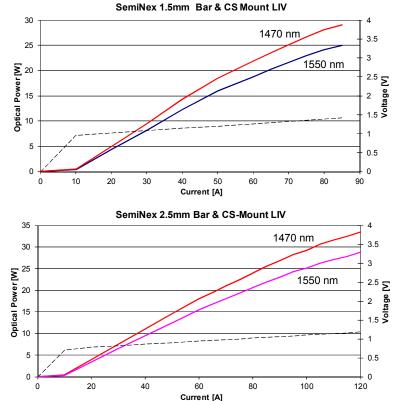
High Power Multi-Mode Laser Bars 25 Watts of CW Power 1470, 1532, and 1550 nm Wavelengths Custom Wavelengths Available

## **Features**

- High output power
- High dynamic power range
- High efficiency
- 19 emitters standard

## **Applications**

- Medical laser equipment
- LIDAR
- Free Space Optical Communication
- DPSS pump lasers
- Military / Aerospace

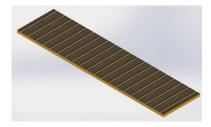


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Laser Bars



**Operating Voltage** 

Series Resistance



1.3

6

1.1

4

		BAR-125	BAR-105	BAR-107	BAR-109	BAR-113	BAR-114	Units
Optical								
Center Wavelength	λα	1355	1460	1480	1540	1550	1570	nm
Expected Optical Power		25	20	25	20	20	25	W
Chip Cavity Length (typical)		1500	1500	2500	1500	1500	2500	μm
Emitter Width	W	95	95	95	95	95	95	μm
Emitter Height	Н	1	1	1	1	1	1	μm
Number of emitters		19	19	19	19	19	19	
Spectral Width	Δλ	15	15	15	15	15	15	nm 3dB
Slope Efficiency	η٥	0.5	0.4	0.31	0.32	0.32	0.27	W/A
Fast Axis Divergence	θ_perp	25	25	25	25	25	25	deg FWHM
Slow Axis Divergence	θ_parallel	8	8	8	8	8	8	deg FWHM
Electrical								
Power conversion Efficiency	η	0.37	0.3	0.25	0.25	0.25	0.23	
Threshold Current	lth	9	10	12	10	10	12	А
Operating Current	lop	50	60	85	65	65	100	Α

1.3

6

1.0

4

1.3

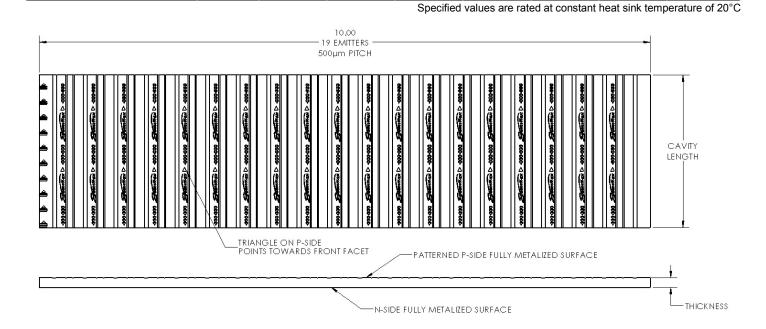
6

1.3

7

Vop

Rs



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